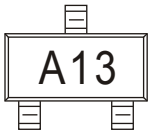
Plastic-Encapsulate Diodes

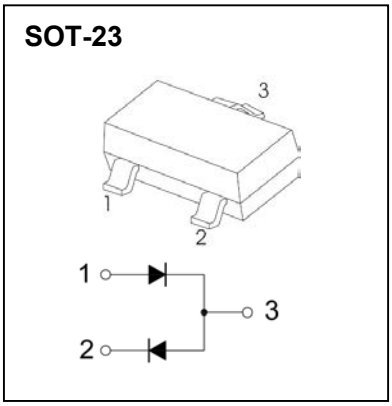
FEATURES

- Low Leakage
- High Conductance

MARKING: A13



SOT-23



Solid dot = Green molding compound device,if none,the normal device.

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_R	DC Blocking Voltage	200	V
I_O	Continuous Forward Current	200	mA
I_{FM}	Peak Forward Current	700	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current @t=8.3ms	2.0	A
P_D	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	357	℃/W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	I_R=5μA	200			V
Reverse current	I_R	V_R=180V			10	nA
Forward voltage	V_F	I_F=1mA			0.75	V
		I_F=10mA			0.85	
		I_F=50mA			0.95	
		I_F=100mA			1.1	
		I_F=200mA			1.3	
		I_F=300mA			1.5	
Total capacitance	C_{tot}	V_R=0V,f=1MHz			4	pF

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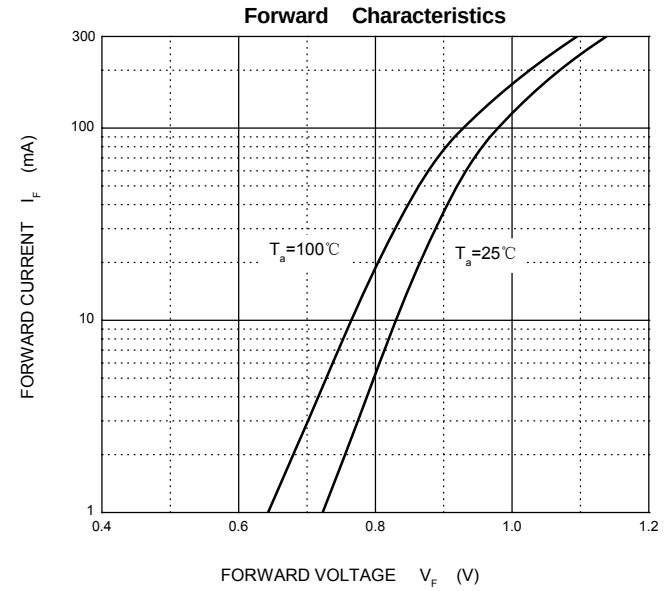
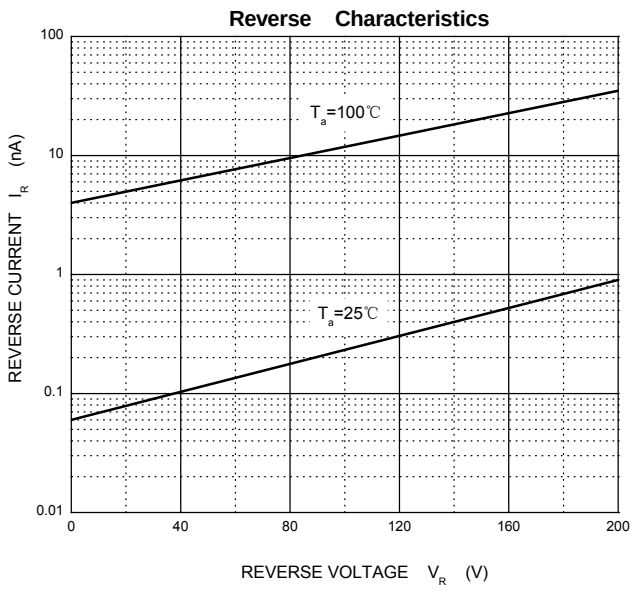
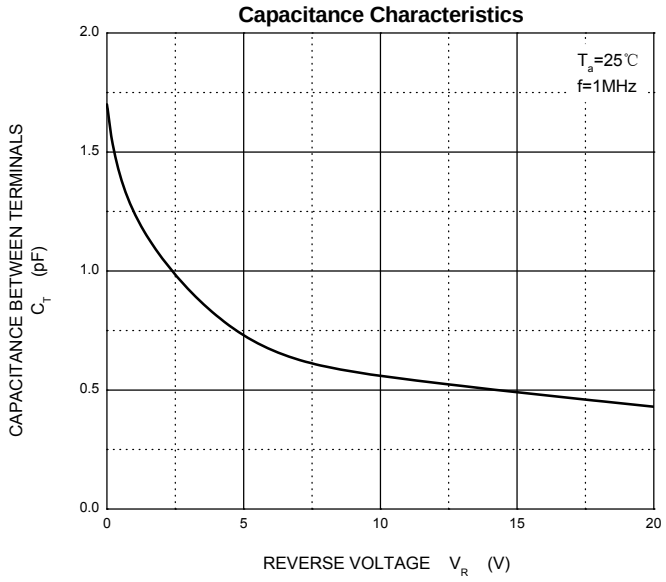
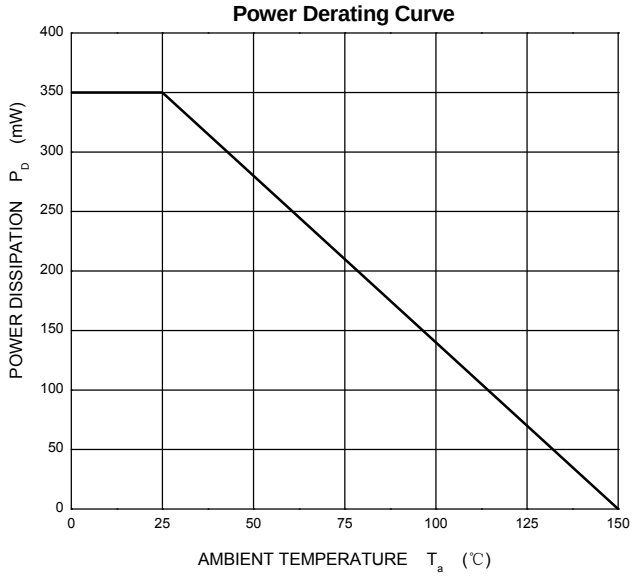
Typical Characteristics









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